Changshu Talent Semiconductors Co.,Ltd
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BAS40-04T
BAS40-05T
BAS40-06T

150mW 40Volt Plastic-Encapsulate Diode

Features

- Pow Dissipation PD=150mW Tamb=25℃
- Forward Current I_F=200mA
- Reverse Voltage V_R=40V
- Epoxy meets UL 94 V-0 flammability rating
- Moisture Sensitivity Level 1

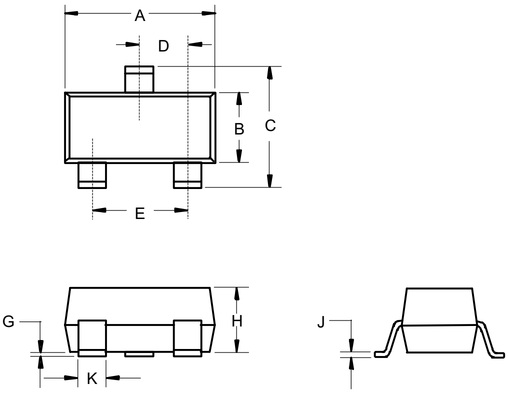
Maximum Ratings

- Operating Temperature: -65℃ to +150℃
- Storage Temperature: -65℃ to +150℃

Electrical Characteristics @ 25°C Unless Otherwise Specified

Reverse Breakdown Voltage	$V_{(BR)R}$	40V	I_R=10µA
Maximum Instantaneous Forward Voltage	V_F	380mV 1000mV	I_{FM} = 1mA; I_{FM} = 40mA;
Maximum DC Reverse Current At Rated DC Blocking Voltage	I_R	200nA	V_R=30Volts
Total Capacitance	C_T	5pF	Measured at 1.0MHz, V_R=0V
Reverse Recovery Time	T_{rr}	5nS	I_F=I_R=10mA, I_{rr}=1mA,R_L=100Ω

SOT-523



DIMENSIONS					
	INCHES		MM		
DIM	MIN	MAX	MIN	MAX	NOTE
A	.059	.067	1.50	1.70	
B	.030	.033	0.75	0.85	
C	.057	.069	1.45	1.75	
D	.020 Nominal		0.50Nominal		
E	.035	.043	0.90	1.10	
G	.000	.004	.000	.100	
H	.028	.031	.70	0.80	
J	.004	.008	.100	.200	
K	.010	.014	.25	.35	

BAS40T/-04T/-05T/-06T

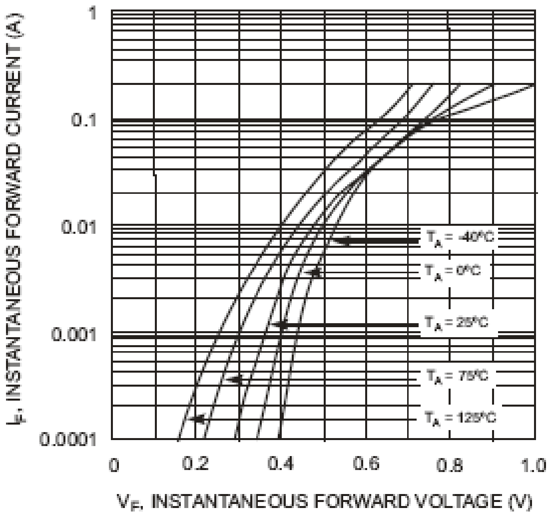


Fig. 1 Typical Forward Voltage

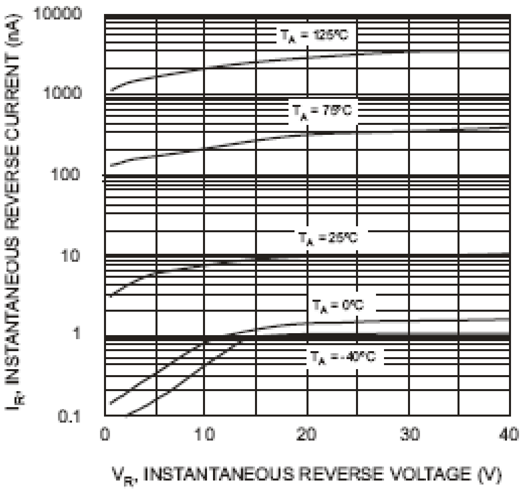


Fig. 2 Typical Reverse Characteristics

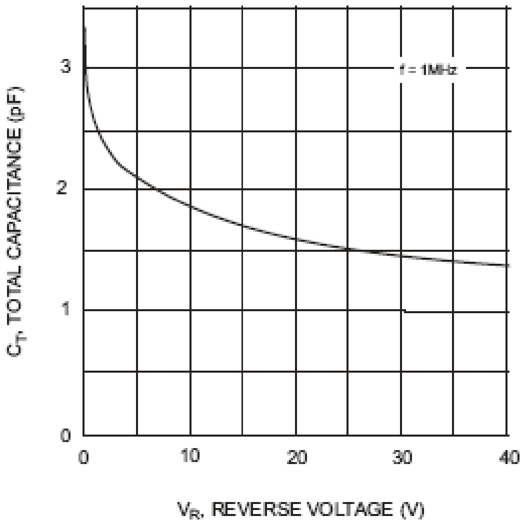


Fig. 3 Typical Capacitance

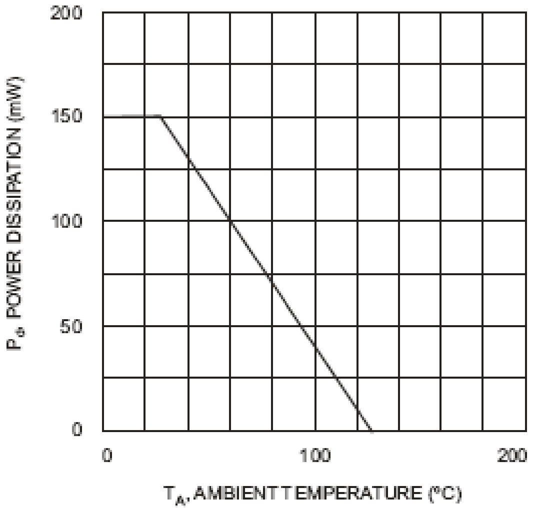
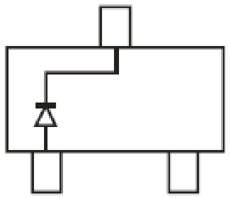


Fig. 4 Power Derating Curve, Total Package

Marking:



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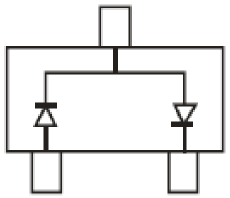

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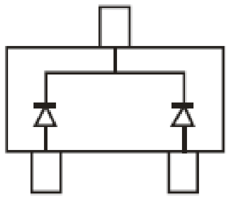

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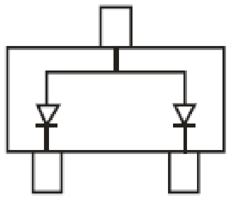

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